TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

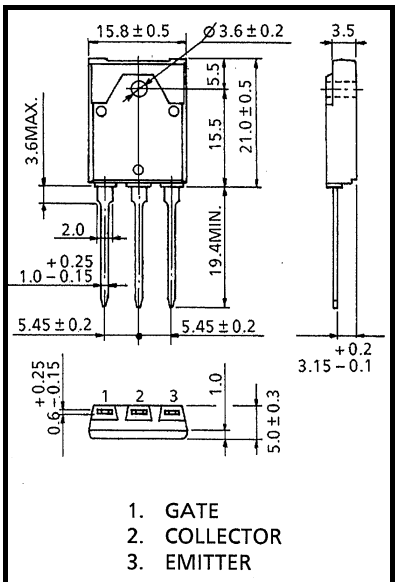
GT30J126

High Power Switching Applications

Fast Switching Applications

- Fourth-generation IGBT
- Enhancement mode type
- Fast switching (FS):
  High speed: t_f = 0.05 μs (typ.)
  Low switching loss: E_{on} = 1.00 mJ (typ.)
  : E_{off} = 0.80 mJ (typ.)
- Low saturation voltage: $V_{CE\ (sat)}$ = 1.95 V (typ.)

Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-16F1A

Weight: 5.8 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

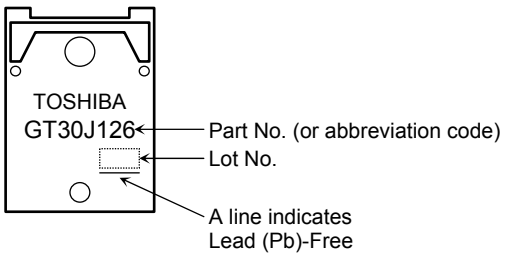
Characteristics		Symbol	Rating	Unit
Collector-emitter voltage		V_{CES}	600	V
Gate-emitter voltage		V_{GES}	±20	V
Collector current	DC	I_C	30	A
	1 ms	I_{CP}	60	
Collector power dissipation (Tc = 25°C)		P_C	90	W
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance	$R_{th\ (j\text{-}c)}$	1.39	°C/W

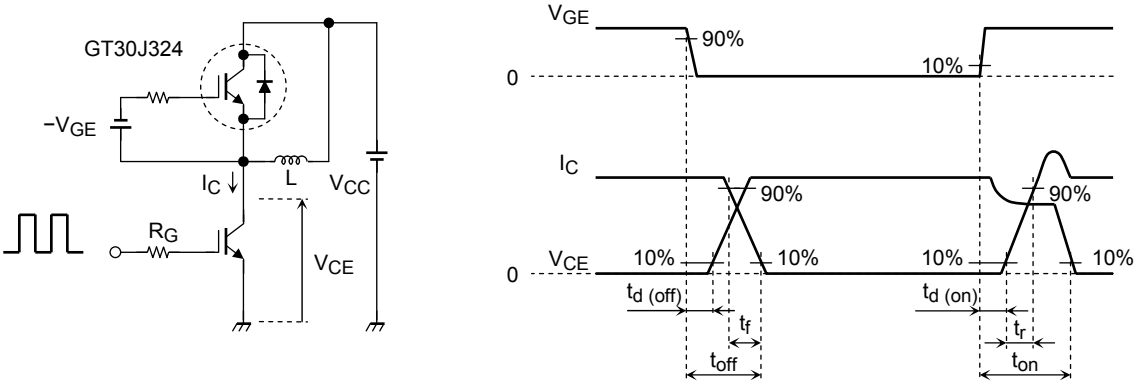
Marking



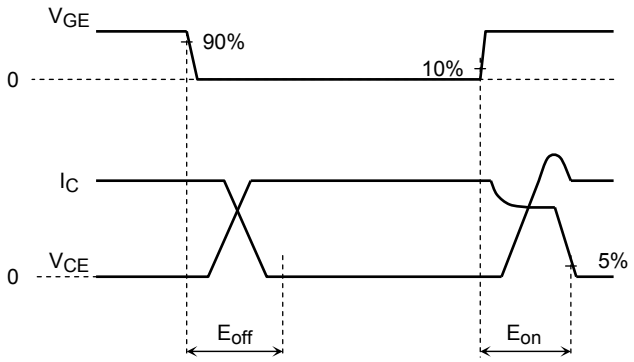
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GES}	V_{GE} = ±20 V, V_{CE} = 0	—	—	±500	nA
Collector cut-off current		I_{CES}	V_{CE} = 600 V, V_{GE} = 0	—	—	1.0	mA
Gate-emitter cut-off voltage		$V_{GE\ (OFF)}$	I_C = 3 mA, V_{CE} = 5 V	3.5	—	6.5	V
Collector-emitter saturation voltage		$V_{CE\ (sat)}$	I_C = 30 A, V_{GE} = 15 V	—	1.95	2.45	V
Input capacitance		C_{ies}	V_{CE} = 10 V, V_{GE} = 0, f = 1 MHz	—	4650	—	pF
Switching time	Turn-on delay time	$t_{d\ (on)}$	Inductive Load V_{CC} = 300 V, I_C = 30 A V_{GG} = +15 V, R_G = 24 Ω (Note 1) (Note 2)	—	0.09	—	μs
	Rise time	t_r		—	0.07	—	
	Turn-on time	t_{on}		—	0.24	—	
	Turn-off delay time	$t_{d\ (off)}$		—	0.30	—	
	Fall time	t_f		—	0.05	—	
	Turn-off time	t_{off}		—	0.43	—	
Switching loss	Turn-on switching loss	E_{on}		—	1.00	—	mJ
	Turn-off switching loss	E_{off}		—	0.80	—	

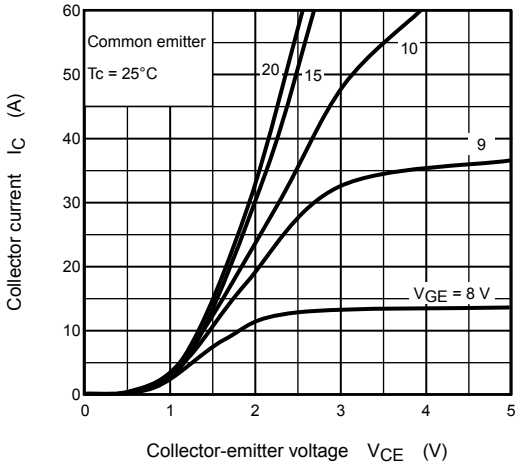
Note 1: Switching time measurement circuit and input/output waveforms



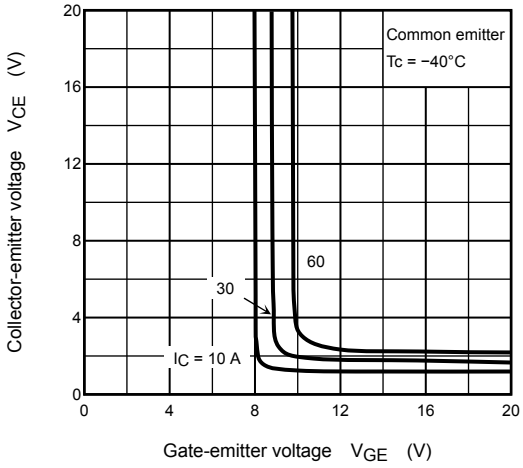
Note 2: Switching loss measurement waveforms



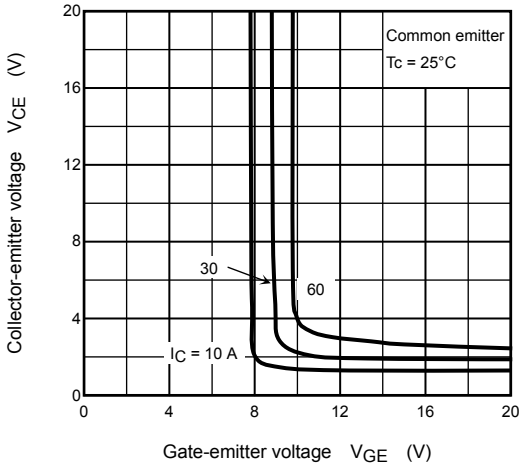
$I_C - V_{CE}$



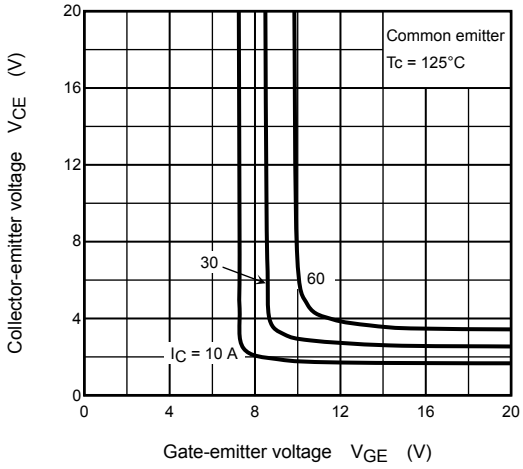
$V_{CE} - V_{GE}$



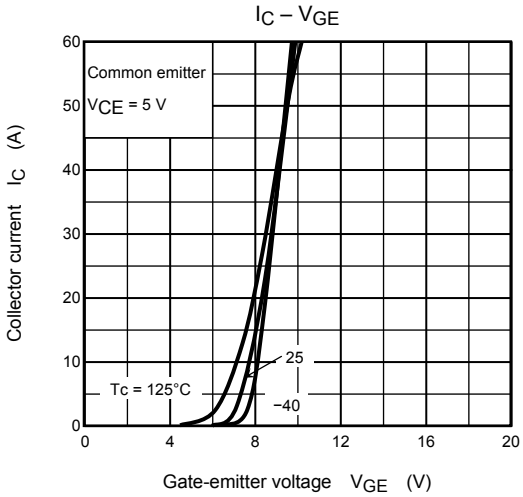
$V_{CE} - V_{GE}$



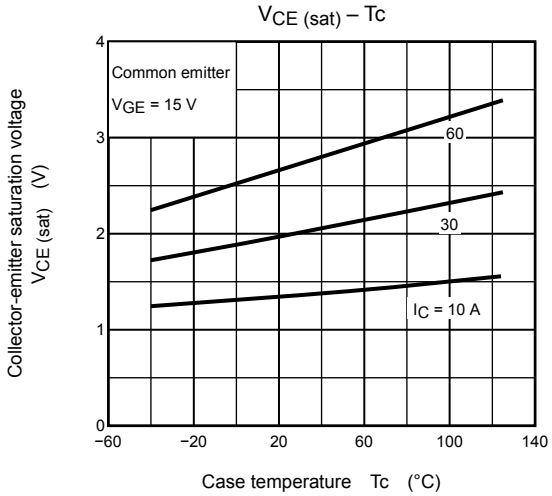
$V_{CE} - V_{GE}$



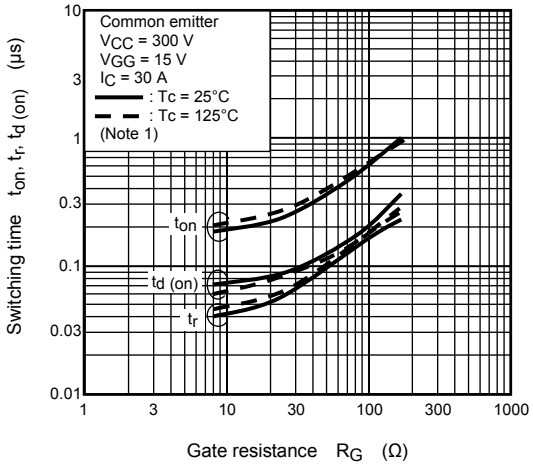
$I_C - V_{GE}$



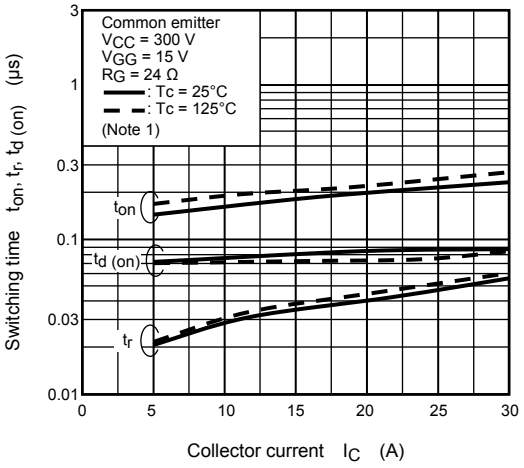
$V_{CE\ (sat)} - Tc$



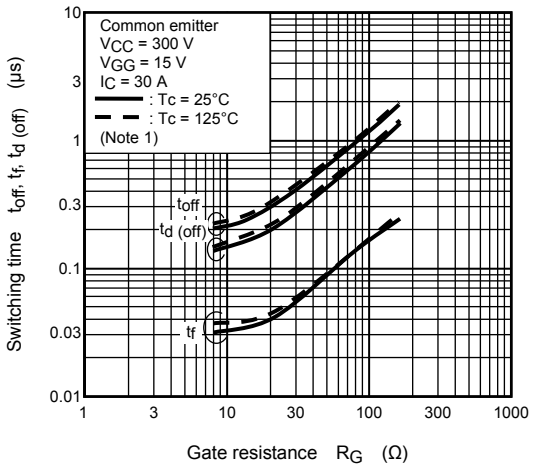
Switching time t_{on}, t_r, $t_{d\ (on)}$ – R_G



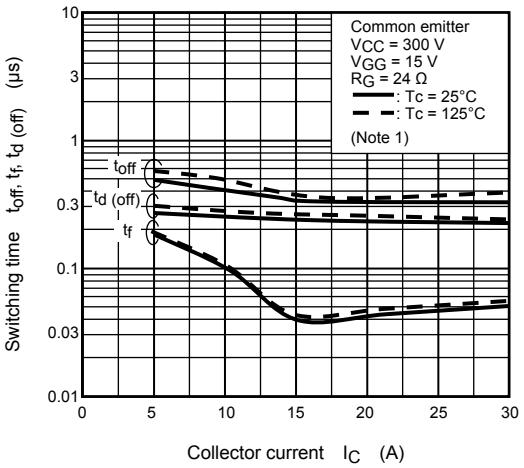
Switching time t_{on}, t_r, $t_{d\ (on)}$ – I_C



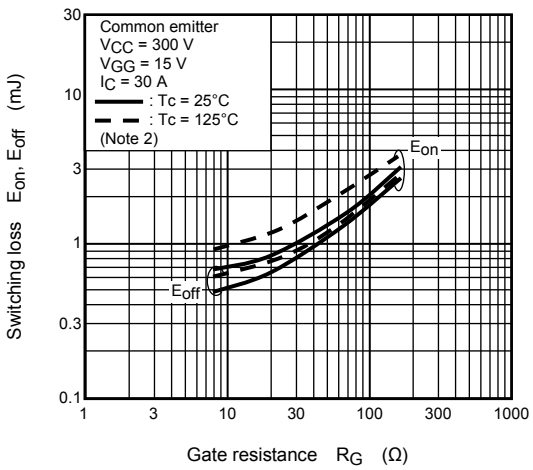
Switching time t_{off}, t_f, $t_{d\ (off)}$ – R_G



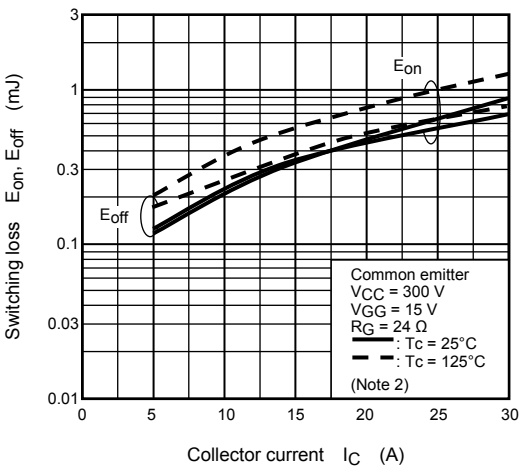
Switching time t_{off}, t_f, $t_{d\ (off)}$ – I_C



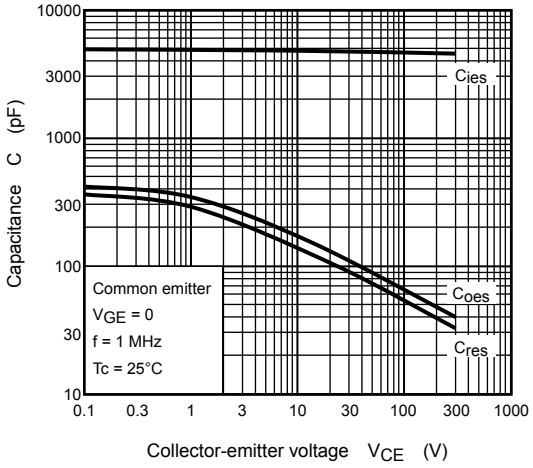
Switching loss E_{on}, E_{off} – R_G



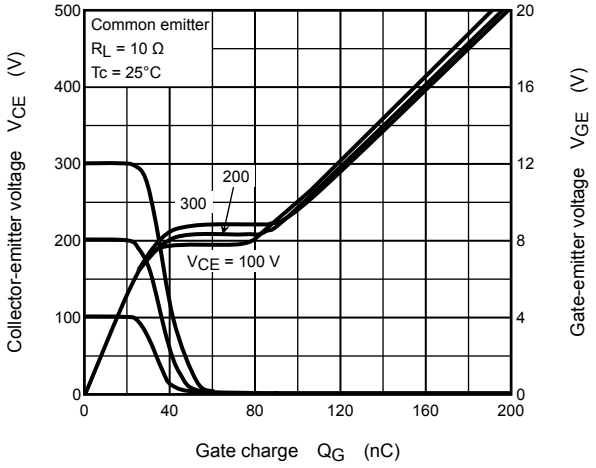
Switching loss E_{on}, E_{off} – I_C



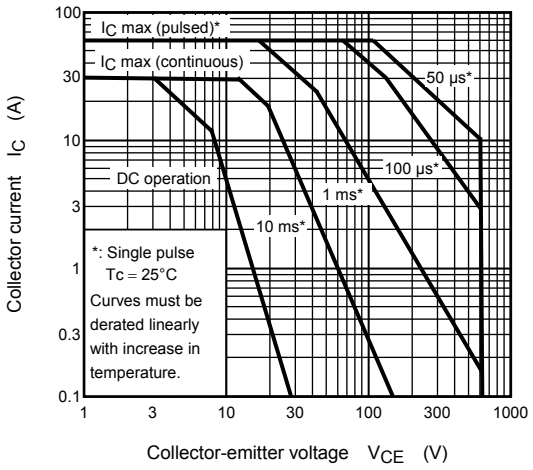
C – V_{CE}



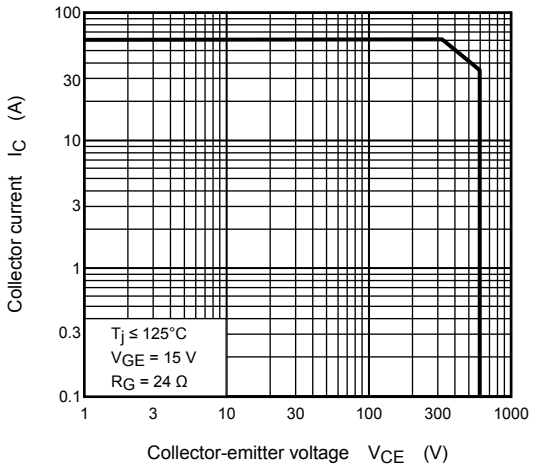
V_{CE}, V_{GE} – Q_G



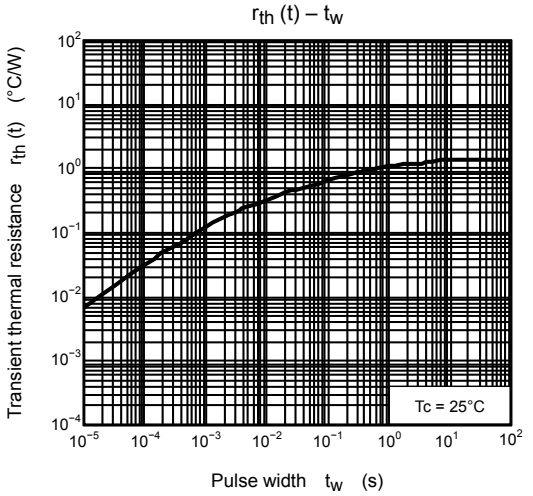
Safe Operating Area



Reverse Bias SOA



r_{th} (t) – t_w



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20070701-EN GENERAL

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